



100V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

#### **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub>           | Ι <sub>D</sub><br>T <sub>C</sub> = +25°C |
|-------------------|-------------------------------|--|
| 100V              | 32mΩ @ V <sub>GS</sub> = 10V  | 33A                                      |
| 1000              | 50mΩ @ V <sub>GS</sub> = 4.5V | 26A                                      |

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

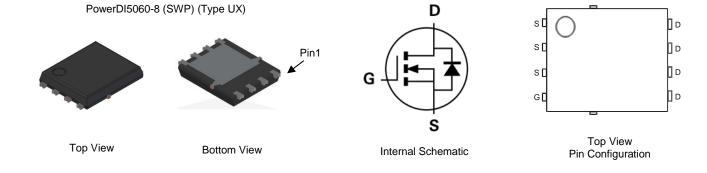
- Synchronous rectifiers
- Backlighting
- Power management functions
- DC-DC converters

#### Features

- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Input Capacitance
- Fast Switching Speed
- Wettable Flank for Improved Optical Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DIODES™ DMTH10H032LPSWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities. <u>https://www.diodes.com/quality/product-definitions/</u>

#### **Mechanical Data**

- Package: PowerDI<sup>®</sup>5060-8 (SWP) (Type UX)
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



# Ordering Information (Note 4)

| Part Number        | Pookage                       | Packing |             |  |
|--------------------|-------------------------------|---------|-------------|--|
|                    | Package                       | Qty.    | Carrier     |  |
| DMTH10H032LPSWQ-13 | PowerDI5060-8 (SWP) (Type UX) | 2,500   | Tape & Reel |  |

Notes: 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# Marking Information



#### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   |   | Symbol           | Value    | Unit |
|--|---|------------------|----------|------|
| Drain-Source Voltage                                     |   | V <sub>DSS</sub> | 100      | V    |
| Gate-Source Voltage                                      |   | V <sub>GSS</sub> | ±20      | V    |
| Continuous Drain Current, V <sub>GS</sub> = 10V (Note 5) | T <sub>C</sub> = +25°C<br>T <sub>C</sub> = +100°C | Ι <sub>D</sub>   | 33<br>23 | А    |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)       |   | I <sub>DM</sub>  | 132      | А    |
| Maximum Continuous Body Diode Forward Current (Not       | e 5)  | Is               | 33       | А    |
| Pulsed Body Diode Forward Current (10µs Pulse, Duty C    | Cycle = 1%)                                       | I <sub>SM</sub>  | 132      | А    |
| Avalanche Current, L = 0.3mH (Note 6)                    |   | I <sub>AS</sub>  | 13       | А    |
| Avalanche Energy, L = 0.3mH (Note 6)                     |   | E <sub>AS</sub>  | 25.3     | mJ   |

#### **Thermal Characteristics**

| Characteristic                                   |                        | Symbol           | Value       | Unit |
|--|------------------------|------------------|-------------|------|
| Total Power Dissipation (Note 7)                 | T <sub>A</sub> = +25°C | PD               | 3.4         | W    |
| Thermal Resistance, Junction to Ambient (Note 7) |                        | R <sub>0JA</sub> | 44          | °C/W |
| Total Power Dissipation (Note 5)                 | T <sub>C</sub> = +25°C | PD               | 68          | W    |
| Thermal Resistance, Junction to Case (Note 5)    |                        | R <sub>θJC</sub> | 2.2         | °C/W |
| Operating and Storage Temperature Range          |                        | TJ, TSTG         | -55 to +175 | °C   |

Notes: 5. Thermal resistance from junction to soldering point (on the exposed drain pad).

6. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ .

7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.



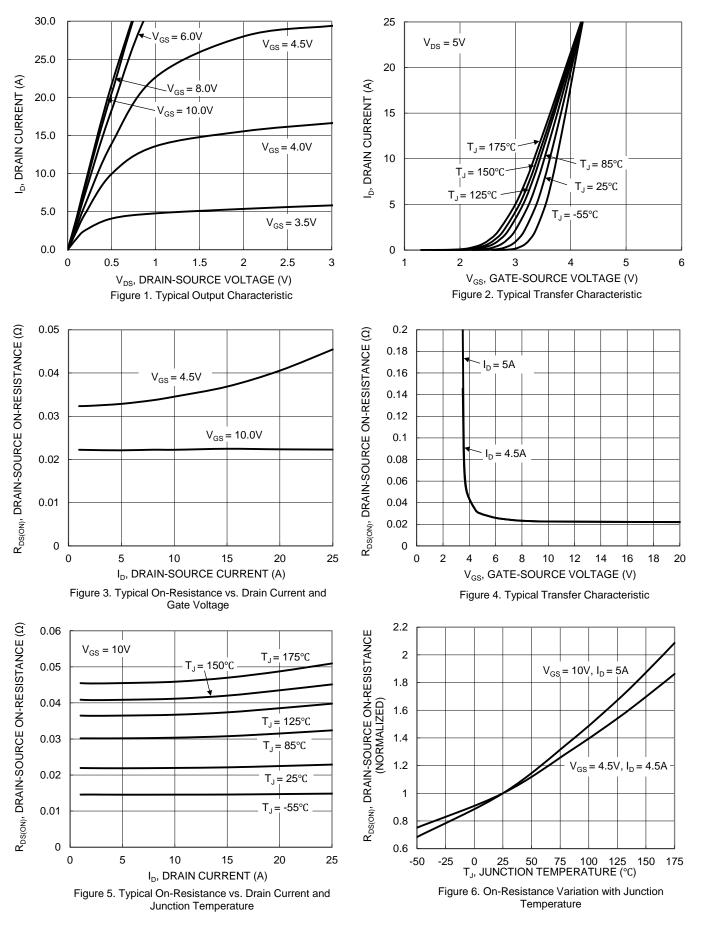
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                             | Symbol              | Min | Тур  | Max  | Unit | Test Condition  |  |
|--|---------------------|-----|------|------|------|---|--|
| OFF CHARACTERISTICS (Note 8)               | ·                   | •   |      | •    | •    | ÷   |  |
| Drain-Source Breakdown Voltage             | BV <sub>DSS</sub>   | 100 | —    | —    | V    | $V_{GS} = 0V, I_D = 1mA$                                |  |
| Zero Gate Voltage Drain Current            | I <sub>DSS</sub>    | —   | —    | 1    | μA   | $V_{DS} = 80V, V_{GS} = 0V$                             |  |
| Gate-Source Leakage                        | I <sub>GSS</sub>    | —   | —    | ±100 | nA   | $V_{GS} = \pm 20V, V_{DS} = 0V$                         |  |
| ON CHARACTERISTICS (Note 8)                |                     |     |      |      |      |   |  |
| Gate Threshold Voltage                     | V <sub>GS(TH)</sub> | 1.3 | —    | 2.5  | V    | $V_{DS} = V_{GS}$ , $I_D = 250 \mu A$                   |  |
| Static Drain-Source On-Resistance          |                     | _   | 22   | 32   |      | $V_{GS} = 10V, I_D = 5A$                                |  |
|  | R <sub>DS(ON)</sub> | —   | 32   | 50   | mΩ   | $V_{GS} = 4.5V, I_D = 4.5A$                             |  |
| Diode Forward Voltage                      | V <sub>SD</sub>     | —   | 0.8  | 1    | V    | $V_{GS} = 0V, I_S = 5A$                                 |  |
| DYNAMIC CHARACTERISTICS (Note 9)           |                     |     |      |      |      |   |  |
| Input Capacitance                          | C <sub>iss</sub>    | —   | 683  | —    | pF   |   |  |
| Output Capacitance                         | C <sub>oss</sub>    | —   | 165  | _    | pF   | V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V<br>f = 1MHz |  |
| Reverse Transfer Capacitance               | C <sub>rss</sub>    | —   | 6.9  | _    | pF   |   |  |
| Gate Resistance                            | R <sub>g</sub>      | —   | 1.2  | —    | Ω    | $V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$                    |  |
| Total Gate Charge (V <sub>GS</sub> = 4.5V) | Qg                  | —   | 6.3  | —    | nC   |   |  |
| Total Gate Charge (V <sub>GS</sub> = 10V)  | Qg                  | —   | 11.9 | _    | nC   |   |  |
| Gate-Source Charge                         | Q <sub>gs</sub>     | —   | 2.0  | _    | nC   | $V_{DS} = 50V, I_D = 6A$                                |  |
| Gate-Drain Charge                          | Q <sub>gd</sub>     | —   | 3.1  | —    | nC   |   |  |
| Turn-On Delay Time                         | t <sub>D(ON)</sub>  | —   | 4.1  | —    | ns   |   |  |
| Turn-On Rise Time                          | t <sub>R</sub>      | —   | 4.5  | —    | ns   | $V_{DS} = 50V, R_{L} = 5.85\Omega$                      |  |
| Turn-Off Delay Time                        | t <sub>D(OFF)</sub> | —   | 12.5 | —    | ns   | $V_{GS} = 10V, R_g = 3\Omega$                           |  |
| Turn-Off Fall Time                         | t <sub>F</sub>      | —   | 9.3  | _    | ns   |   |  |
| Reverse Recovery Time                      | t <sub>RR</sub>     | —   | 31.5 | —    | ns   |   |  |
| Reverse Recovery Charge                    | Q <sub>RR</sub>     |     | 94.6 | —    | nC   | I <sub>F</sub> = 6A, dI/dt = 500A/µs                    |  |

Notes:8. Short duration pulse test used to minimize self-heating effect.9. Guaranteed by design. Not subject to product testing.

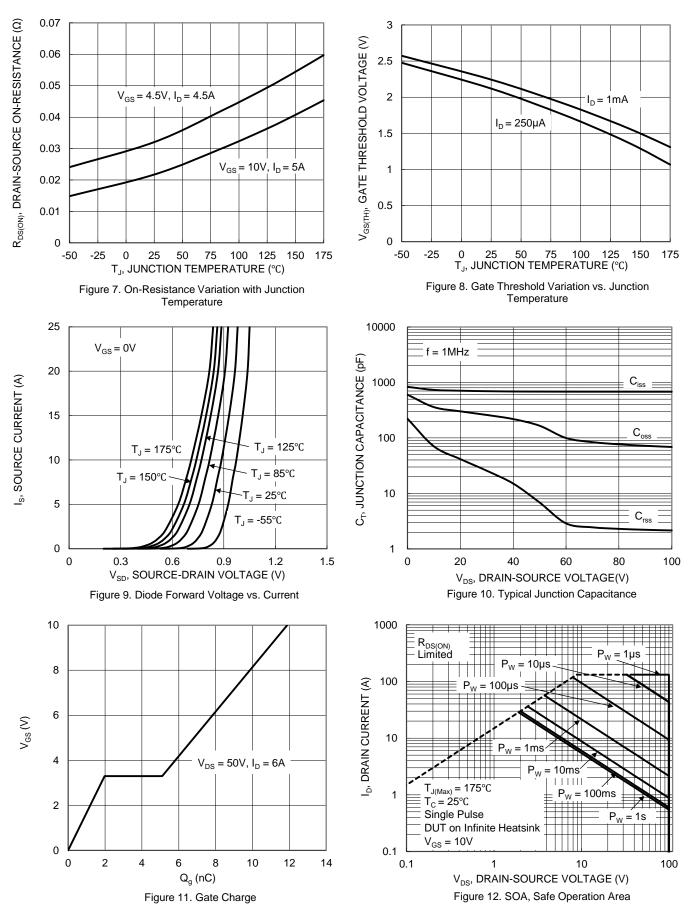


# DMTH10H032LPSWQ





### DMTH10H032LPSWQ



DMTH10H032LPSWQ Document number: DS44569 Rev. 3 - 2



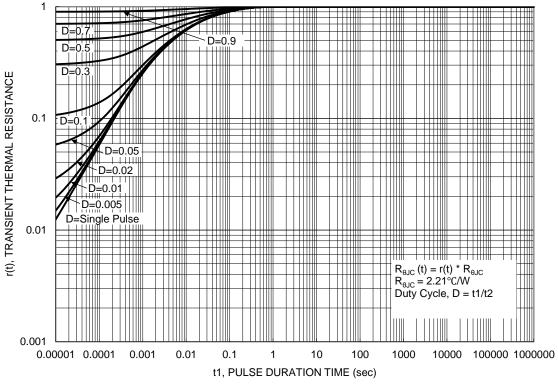
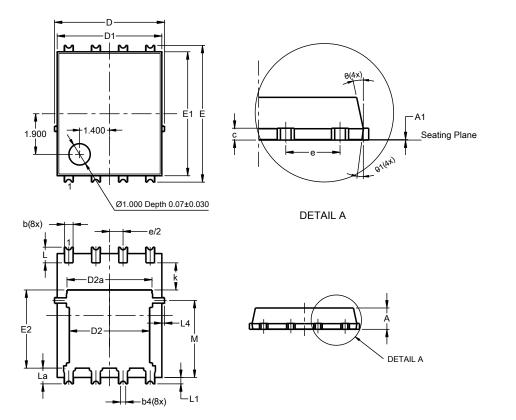


Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



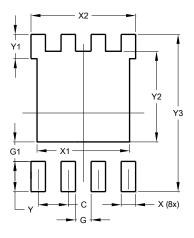
|               |       | ( <b>T</b> 11)() |
|---------------|-------|------------------|
| PowerDI5060-8 | (SWP) | (Type UX)        |

| PowerDI5060-8 (SWP) |                      |         |       |  |  |
|---------------------|----------------------|---------|-------|--|--|
| (Type UX)           |                      |         |       |  |  |
| Dim                 | Min                  | Max     | Тур   |  |  |
| Α                   | 0.90                 | 1.10    | 1.00  |  |  |
| A1                  | 0                    | 0.05    | -     |  |  |
| b                   | 0.30                 | 0.50    | 0.41  |  |  |
| b2                  | 0.20                 | 0.35    | 0.25  |  |  |
| b4                  | (                    | ).25REF | -     |  |  |
| С                   | 0.230                | 0.330   | 0.277 |  |  |
| D                   |                      | .15 BS0 | 2     |  |  |
| D1                  | 4.70                 | 5.10    | 4.90  |  |  |
| D2                  | 3.56                 | 3.96    | 3.76  |  |  |
| D2a                 | 3.78                 | 4.18    | 3.98  |  |  |
| Е                   | 6                    | .40 BS0 | 2     |  |  |
| E1                  | 5.60                 | 6.00    | 5.80  |  |  |
| E2                  | 3.46                 | 3.86    | 3.66  |  |  |
| E2a                 | 4.195                | 4.595   | 4.395 |  |  |
| е                   | 1                    | .27BSC  | )     |  |  |
| k                   | 1.05                 |         | -     |  |  |
| L                   | 0.635                | 0.835   | 0.735 |  |  |
| La                  | 0.635                | 0.835   | 0.735 |  |  |
| L1                  | 0.200                | 0.400   | 0.300 |  |  |
| L1a                 | 0                    | .050RE  |       |  |  |
| L4                  | 0.025                | 0.225   | 0.125 |  |  |
| М                   | 3.205                | 4.005   | 3.605 |  |  |
| θ                   | 10°                  | 12°     | 11°   |  |  |
| θ1                  | 6°                   | 8°      | 7°    |  |  |
| All                 | All Dimensions in mm |         |       |  |  |

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (SWP) (Type UX)



| Dimensions | Value   |
|------------|---------|
| Dimensions | (in mm) |
| С          | 1.270   |
| G          | 0.660   |
| G1         | 0.820   |
| Х          | 0.610   |
| X1         | 4.100   |
| X2         | 4.420   |
| Y          | 1.270   |
| Y1         | 1.020   |
| Y2         | 3.810   |
| Y3         | 6.610   |



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 1N4148WS-7-F